

REMARKS

Claims 7, 12 and 13 have been amended. No new matter has been introduced by these amendments.

Claims 1-6 have previously been cancelled.

Claims 7-15 are thus pending in the application.

In the Office Action, claims 7-15 were rejected under 35 U.S.C. § 102(e) as being anticipated by U.S. Publication No. 2006/0152655 to Kim.

Rejections Under 35 U.S.C. § 102(e)

The rejections under 35 U.S.C. § 102(e) are respectfully traversed.

With respect to claim 1, Kim does not disclose or teach a thin film transistor array panel comprising a first thin film transistor connected to the first gate line and the data line, and including a first drain electrode overlapping the second gate line; a second thin film transistor connected to the second gate line and the data line, disposed opposite the first thin film transistor with respect to the data line, and including a second drain electrode overlapping the first gate line," as recited in amended claim 1.

Kim discloses a data wire formed on an ohmic contact layer 163 and 165 or a gate insulating layer 140. The data wire includes a plurality of data lines 171, 173 and 179 extending in a longitudinal direction and intersecting the gate lines 121 to define a plurality of pixel areas. Kim further discloses a plurality of drain electrodes 175 of TFTs formed on other portions 165 of the ohmic contact layer, located opposite the source electrodes 173 with respect to the gate electrodes 123. Each drain electrode 175 is separated from the data lines 171, 173 and 179 and placed opposite to the corresponding source electrode 173 with respect to the corresponding gate electrode 123 or a channel portion C of the TFT. *See* paragraph [0070].

Applicant respectfully submits that there is nothing in Kim that discloses or teaches a first thin film transistor connected to the first gate line and the data line, and including a first drain electrode overlapping the second gate line. Kim discloses a plurality of source electrodes 173 of TFTs branched from the data line 171 and overlaps a gate line 121. Each drain electrode 175 of a data wire is separated from the data line units 171, 173 and 179 and placed opposite to the corresponding source electrode 173 with respect to the corresponding gate electrode 123 or the channel portion C of the TFT. *See* paragraph [0070] and Figure 8. There is nothing in Kim that discloses or teaches that a first thin film transistor is connected to the first gate line and the data line, and a first drain electrode of the first thin film transistor overlaps a **second gate line**. The drain electrode 175 of Kim is separated from the data line units 171, 173 and 179 and overlaps a first gate line 121.

Applicant further submits that there is nothing in Kim that discloses or teaches a second thin film transistor connected to the **second gate line** and the data line, **disposed opposite the first thin film transistor** with respect to the data line, and including a **second drain electrode overlapping the first gate line**. Kim further discloses a plurality of drain electrodes 175 of TFTs formed on other portions 165 of the ohmic contact layer, located opposite the source electrodes 173 with respect to the gate electrodes 123. Each drain electrode 175 is separated from the data lines 171, 173 and 179 and placed opposite to the corresponding source electrode 173 with respect to the corresponding gate electrode 123 or a channel portion C of the TFT. *See* paragraph [0070] and Figure 8. There is nothing in Kim that discloses or teaches that a **second thin film transistor** is connected to a **second gate line**. The thin film transistor of Kim is connected to the first gate line 121 and data line 171. Moreover, there is nothing in Kim that discloses or teaches a second thin film transistor that is **disposed opposite the first thin film transistor with respect to the data line**. Kim discloses that the plurality of drain electrodes 175 of TFTs are formed on other portions 165 of the ohmic contact layer, located **opposite the source electrodes 173 with respect to the gate electrodes 123**. Further, there is nothing in Kim that discloses or teaches that a second thin film transistor includes a second drain electrode which overlaps the first gate line, and

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that the first thin film transistor and the second thin film transistor are both connected to one data line and are located opposite sides of the data line.

In view of the above arguments, Kim does not anticipate independent claim 1. Therefore the rejection of independent claim 1, as well as dependent claims 2-15, which incorporates all of the limitations of its respective base claim 1, should be withdrawn based on the above arguments.

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CONCLUSION

Applicant submits that such amendments and arguments are fully responsive to the Office Action dated June 23, 2008 and respectfully requests the asserted grounds of rejections be withdrawn based on such arguments.

In view of the above, it is believed that the above-identified application is in condition for allowance, and notice to that effect is respectfully requested. Should the Examiner have any questions, the Examiner is encouraged to contact the undersigned at the telephone number indicated below.

If there are any charges due with respect to this Amendment or otherwise, please charge them to Deposit Account No. 06-1130 maintained by Applicant's Attorneys.

Respectfully submitted,
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